## NSN 5961-01-580-9280

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-580-9280 **Inclosure Material:** Plastic **Overall Length:** 3.0 millimeters **Overall Height:** 1.1 millimeters **Overall Width:** Between 1.5 millimeters and 1.7 millimeters **Function For Which Designed:** Amplifier **End Application:** Ca70608-00 (19156), receiver-transmitter Joint Electronic Device Engineering Council/jedec/case Outline Designation: Mo-193, var.Aa, issue c, dated january 2000 **Component Name And Quantity:** 2 transistor **Mounting Method:** Press fit **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 collector to emitter voltage, dc all transistor and 60.0 collector to base voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 600.00 milliamperes collector current, dc all transistor **Power Rating Per Characteristic:** 700.0 milliwatts total power dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Product Name:** Dwg- cage 19156: transistor array, general purpose amplifier; dwg- cage 7d893: pnp multi-chip general purpose amplifier **Special Features:** Fairchild pkg: supersot-6 **Terminal Type And Quantity:** 6 tab, solder lug Shelf Life: N/a **Unit Of Measure:** 

Fiig: A110a0

No

**Demilitarization:**